鲁晶®

2N4402

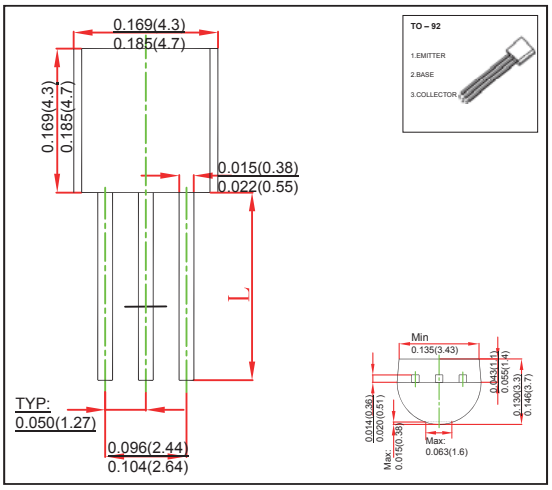
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Switching and amplification in high voltage
- Applications such as telephony
- Low current
- High voltage
- PNP Transistors

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.6	A
Collector Power Dissipation	K_D	625	mW
Thermal Resistance, junction to Ambient	R_{KJA}	200	℃ /W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55~+150	℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V,I_E=0			-0.1	
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-1mA	30			
		V_{CE}=-1V, I_C=-10mA	50			
		V_{CE}=-2V, I_C=-150mA	50		150	
		V_{CE}=-2V, I_C=-500mA	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-150mA,I_B=-15mA			-0.4	V
		I_C=-500mA,I_B=-50mA			-0.75	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=-150mA,I_B=-15mA	-0.75		-0.95	V
		I_C=-500mA,I_B=-50mA			-1.3	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz			8.5	pF
Emitter input capacitance	C_{ib}	V_{EB}=-0.5V,I_C=0, f=1MHz			30	pF
Transition frequency	f_T	V_{CE}=-10V,I_C=-20mA, f=100MHz	150			MHz

*Pulse test: pulse width ≤300ᵛs, duty cycle≤ 2.0%.